A METHOD AND STRUCTURE FOR IMPROVED ALIGNMENT TOLERANCE IN MULTIPLE, SINGULARIZED PLUGS

Abstract of the Disclosure

An improved method and structure which increases the alignment tolerances in multiple, singularized plugs are provided. The invention discloses a novel method for forming individual plug contacts with increased surface area for improved registration between semiconducting layers. Also the improved plug contacts are particularly well suited to receiving contact formations which have any taper to them. IGFETS and other devices formed from this design can be used in a variety of beneficial applications, e.g. logic or memory.

"Express Mail" mailing label number: <u>EL873859154US</u>
Date of Deposit: <u>December 4, 2001</u>

This paper or fee is being deposited on the date indicated above with the United States Postal Service pursuant to 37 CFR 1.10, and is addressed to U.S. Patent and Trademark Office, Box Patent Application, P.O. Box 2327, Arlington, VA 22202.